



IIT Bombay Nanofabrication Facility

Tool Name: ALD LL (Atomic Layer Deposition Load Lock)

Glimpse

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Photograph



ALD LL system uses reactive chemistry to generate thin films one atomic layer at a time has a remote inductively coupled plasma source to allow for low temperature ALD depositions

Model: Cambridge Nanotech Fiji 200 with load lock

Specifications

1. **Type of deposition:** HfO₂, Al₂O₃, TiO₂, TiN, AlN
2. **Type of substrate:** Silicon, germanium
3. **Temperature for deposition:** 100 to 300 degrees Celsius
4. **Process gas used:** Oxygen, Argon, Nitrogen, Ammonia

Process Capabilities

1. Silicon or germanium wafer of size 10 mm to 6 inch can be deposited
2. Multi-layer deposition can be done